

AMENDMENTS TO THE SPECIFICATION

Please insert the following paragraph after paragraph 11 and before paragraph 12:

According to another exemplary embodiment of the present invention, a thin film transistor substrate comprises: an insulating substrate; a low voltage driving thin film transistor formed above said insulating substrate, wherein said low voltage driving thin film transistor comprises a first active layer formed above said insulating substrate, a first gate insulating film formed on said first active layer, and a first gate electrode driven at low voltage formed on said first gate insulating film; and a high voltage driving thin film transistor formed above said insulating substrate, wherein said high voltage driving thin film transistor comprises a second active layer formed above said insulating substrate, and a second gate insulating film formed on said second active layer, a second gate electrode driven at high voltage formed on said second gate insulating film, wherein said second gate insulating film comprises said first gate insulating film and a gate cover film formed above said first gate insulating film, wherein said second active layer has at least two impurity doping regions which overlap said second gate electrode, wherein said first active layer has at least two impurity doping regions formed in a self aligning manner with respect to said first gate electrode, wherein said high voltage driving thin film transistor further comprises a third gate electrode driven at low voltage, wherein a gate length of said third gate electrode is shorter than a gate length of said second gate electrode, wherein said third gate electrode is formed between said second active layer and said second gate electrode and on the first gate insulating film, wherein said third gate electrode is formed of the same material as said first gate electrode, and wherein said third gate electrode has the same thickness as said first gate electrode.